NGD15N41CL

Product Preview

Ignition IGBT 15 Amps, 410 Volts

N-Channel DPAK

This Logic Level Insulated Gate Bipolar Transistor (IGBT) features monolithic circuitry integrating ESD and Over–Voltage clamped protection for use in inductive coil drivers applications. Primary uses include Ignition, Direct Fuel Injection, or wherever high voltage and high current switching is required.

- Ideal for Coil-on-Plug Applications
- DPAK Package Offers Smaller Footprint and Increased Board Space
- Gate–Emitter ESD Protection
- Temperature Compensated Gate–Collector Voltage Clamp Limits Stress Applied to Load
- Integrated ESD Diode Protection
- New Cell Design Increases Unclamped Inductive Switching (UIS) Energy Per Area
- Short-Circuit Withstand Capability
- Low Threshold Voltage to Interface Power Loads to Logic or Microprocessor Devices
- Low Saturation Voltage
- High Pulsed Current Capability
- Optional Gate Resistor (RG) and Gate-Emitter Resistor (RGE)

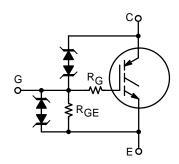
MAXIMUM RATINGS (T_J = 25°C unless otherwise noted)

Rating	Symbol	Value	Unit
Collector–Emitter Voltage	VCES	440	VDC
Collector-Gate Voltage	VCER	440	V_{DC}
Gate–Emitter Voltage	VGE	15	V _{DC}
Collector Current–Continuous @ T _C = 25°C	IC	15	A _{DC}
Operating and Storage Temperature Range	TJ, T _{stg}	–55 to 175	°C



http://onsemi.com

15 AMPS 410 VOLTS VCE(on) = 2.1 V MAX



MARKING DIAGRAM



DPAK CASE 369A STYLE 2



TBD = Specific Device Code

ORDERING INFORMATION

Device	Package	Shipping		
NGD15N41CL	DPAK	75 Units/Rail		
NGD15N41CLT4	DPAK	2500/Tape & Reel		

This document contains information on a product under development. ON Semiconductor reserves the right to change or discontinue this product without notice.

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UNCLAMPED DRAIN-TO-SOURCE AVALANCHE CHARACTERISTICS (T.1 < 150°C)

Characteristic Single Pulse Collector–to–Emitter Avalanche Energy VCC = 50 V, VGE = 5 V, Pk I _L = 16 A, L = 1.8 mH, Starting T _J = 25°C VCC = 50 V, VGE = 5 V, Pk I _L = 15 A, L = 1.8 mH, Starting T _J = 150°C		Symbol E _{AS}		Value		Unit mJ		
				225 200				
THERMAL CHARACTERISTICS								
Thermal Resistance, Junction to Ambient		DPAK	$R_{\theta JA}$	\	100		°C/W	
Maximum Lead Temperature for Soldering Purposes	s, 1/8" from case fo	or 5 seconds	conds T _L		275		°C	
ELECTRICAL CHARACTERISTICS (T _C = 25°C	unless otherwise r	noted)						
Characteristic	Symbol	Test Cond	ditions	Min	Тур	Max	Unit	
OFF CHARACTERISTICS								
Collector–Emitter Clamp Voltage	BVCES	$I_C = 2 \text{ r}$ $T_J = -40^{\circ}\text{C t}$		380	410	440	V _{DC}	
Zero Gate Voltage Collector Current	ICES	V _{CE} = 30 V _{GE} = 0, T _J		Ι	-	40	μA _{DC}	
		V _{CE} = 30 V _{GE} = 0, T _J	00 V, = 150°C	-	-	200		
Reverse Collector–Emitter Leakage Current	l _{ECS}	V _{CE} = -	-24 V	-	_	1.0	mA	
Gate-Emitter Clamp Voltage	BVGES	lG = 5 i	mA	10	_	16	VDC	
Gate Resistor (Optional)	RG			Ī	70	-	Ω	
Gate Emitter Resistor (Optional)	R _{GE}			10		26	kΩ	
ON CHARACTERISTICS*								
Gate Threshold Voltage	VGE(th)	IC = 1 i		1.0	1.4	2.1	VDC	
Threshold Temperature Coefficient (Negative)	-			-	4.4	_	mV/°C	
Collector-to-Emitter On-Voltage	V _{CE(on)}	I _C = 6 A, V _C	3E = 4 V	ı	-	1.8	V _{DC}	
Collector-to-Emitter On-Voltage	VCE(on)	I _C = 10 V _{GE} = 4 T _J = 15	4.5 V,	-	-	2.1	V _{DC}	
DYNAMIC CHARACTERISTICS								
Input Capacitance	C _{ISS}	V _{CC} = 1	15 V		700		pF	
Output Capacitance	Coss	V _{GE} =		_	60	_	1	
Transfer Capacitance	C _{RSS}		f = 1 MHz		6.0		1	
SWITCHING CHARACTERISTICS*								
Turn–Off Delay Time	^t d(off)	V _{CC} = 30			4.0	-	μSec	
Fall Time	t _f	R _G = 1 L = 300		ı	10	-	1 _	
Turn-On Delay Time	^t d(on)	V _{CC} = 1	0 V, .5 A	-	1.0	-	μSec	
	$\overline{}$	+			+		-	

^{*}Pulse Test: Pulse Width $\leq 300 \,\mu\text{S}$, Duty Cycle $\leq 2\%$.

Rise Time

 t_{r}

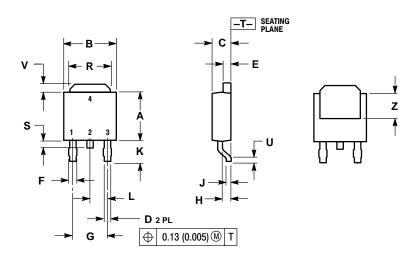
 $R_G = 1 \text{ k}\Omega,$ $R_L = 1 \Omega$

4.0

NGD15N41CL

PACKAGE DIMENSIONS

DPAK CASE 369A-13 **ISSUE AA**



- NOTES:
 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 2. CONTROLLING DIMENSION: INCH.

	INC	HES	MILLIMETERS		
DIM	MIN	MAX	MIN	MAX	
Α	0.235	0.250	5.97	6.35	
В	0.250	0.265	6.35	6.73	
С	0.086	0.094	2.19	2.38	
D	0.027	0.035	0.69	0.88	
Е	0.033	0.040	0.84	1.01	
F	0.037	0.047	0.94	1.19	
G	0.180 BSC		4.58 BSC		
Н	0.034	0.040	0.87	1.01	
J	0.018	0.023	0.46	0.58	
K	0.102	0.114	2.60	2.89	
L	0.090	BSC	2.29	9 BSC	
R	0.175	0.215	4.45	5.46	
S	0.020	0.050	0.51	1.27	
U	0.020		0.51		
٧	0.030	0.050	0.77	1.27	
7	0 138		3.51		

STYLE 2: PIN 1. GATE 2. DRAIN 3. SOURCE 4. DRAIN

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